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Publication

A fourfold coordinated point defect in silicon

JournalArticle (Originalarbeit in einer wissenschaftlichen Zeitschrift)

ID 2832515

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Year 2002

Title A fourfold coordinated point defect in silicon

Journal Physical Review Letters

Volume 88

Number 23

Pages / Article-Number 235501

Vacancies, interstitials, and Frenkel pairs are considered to be the basic point defects in silicon. We challenge this point of view by presenting density functional calculations that show that there is a stable point defect in silicon that has fourfold coordination and is lower in energy than the traditional defects.

Publisher American Physical Society

ISSN/ISBN 0031-9007 ; 1079-7114

edoc-URL <https://edoc.unibas.ch/73856/>

Full Text on edoc No;

Digital Object Identifier DOI 10.1103/PhysRevLett.88.235501

PubMed ID <http://www.ncbi.nlm.nih.gov/pubmed/12059373>

ISI-Number 000175860500035

Document type (ISI) Article